N-channel 30 V 6.5 m $\Omega$  logic level MOSFET in LFPAK using NextPower technology

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

SOT669 (LFPAK; Power-SO8)

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN6R0-30YLB	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	30	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{M}}$	-	71	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	50	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$ ; see Figure 4	-	283	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	58	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
$V_{ESD}$	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	210	-	V
Source-dra	ain diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	53	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	283	Α
Avalanche	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 71 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 Ω; unclamped; see Figure 3	-	13	mJ

PSMN6R0-30YLB

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### N-channel 30 V 6.5 m $\Omega$ logic level MOSFET in LFPAK using NextPower technology

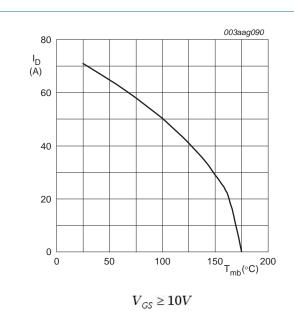


Fig 1. Continuous drain current as a function of mounting base temperature

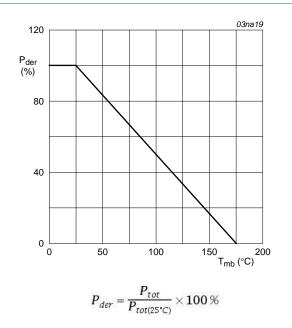


Fig 2. Normalized total power dissipation as a function of mounting base temperature

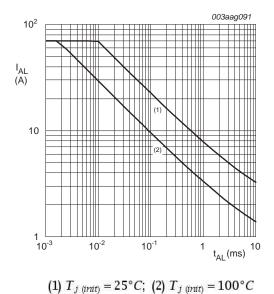


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

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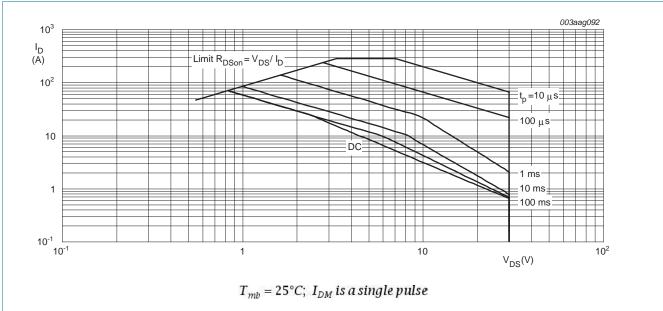


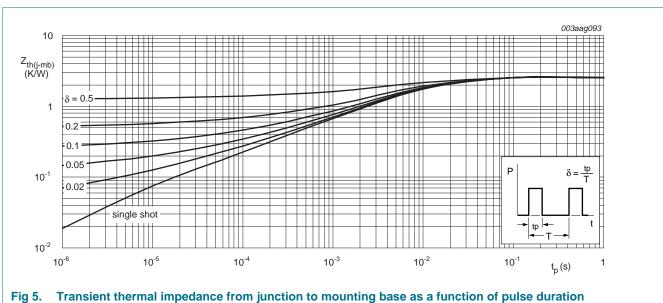
Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

N-channel 30 V 6.5 mΩ logic level MOSFET in LFPAK using NextPower technology

## **Thermal characteristics**

#### Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	2.35	2.57	K/W



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N-channel 30 V 6.5 mΩ logic level MOSFET in LFPAK using NextPower technology

## **Characteristics**

Table 6. **Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see Figure 10; see Figure 11	1.05	1.48	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nΑ
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C}; \text{see}$ Figure 12	-	6.9	8.1	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	13.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	5.5	6.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	10.7	mΩ
$R_G$	gate resistance	f = 1 MHz	-	1.62	3.24	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub> total gate charge	$I_D = 20 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	19	-	nC	
		$I_D = 20 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see Figure 14; see Figure 15	-	9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 15	-	17	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	2.6	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	0.6	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.6	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 20 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.39	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1088	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	278	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	78	-	pF
d(on)	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$	-	16	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	15	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	29	-	ns
t <sub>f</sub>	fall time		-	9	-	ns

**Product data sheet** 

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	7.2	-	nC
Source-dra	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 20 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.85	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	25.5	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	15	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 20 \text{ A};$	-	15.9	-	ns
t <sub>b</sub>	reverse recovery fall time	$dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{DS} = 15 \text{ V}$ ; see Figure 18	-	9.6	-	ns

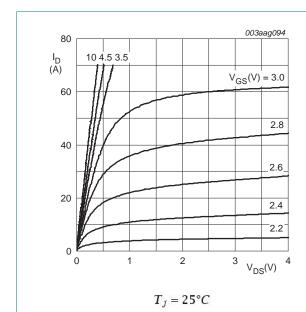


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

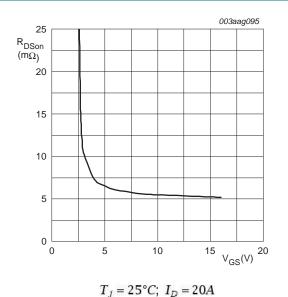


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

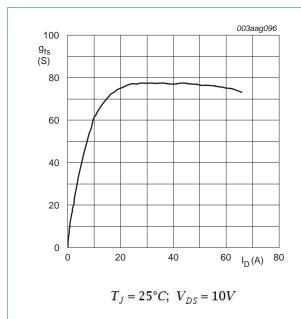


Fig 8. Forward transconductance as a function of drain current; typical values

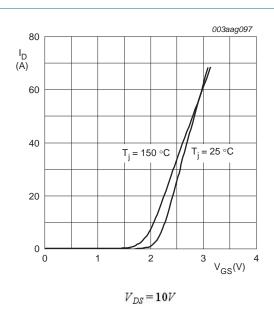


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

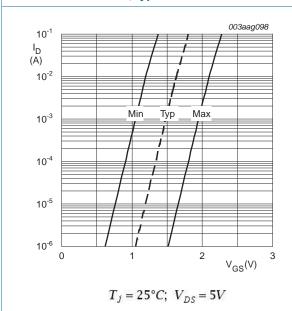


Fig 10. Sub-threshold drain current as a function of gate-source voltage

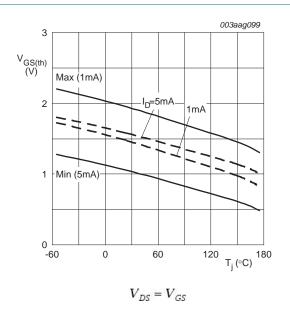


Fig 11. Gate-source threshold voltage as a function of junction temperature

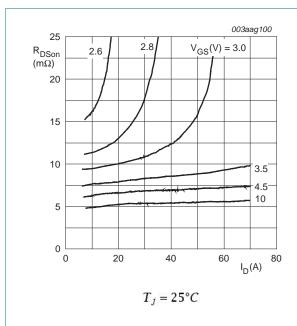


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

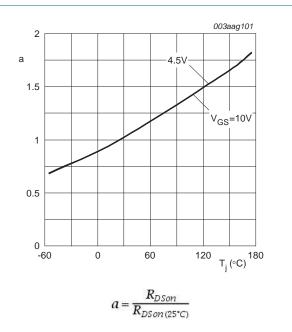


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

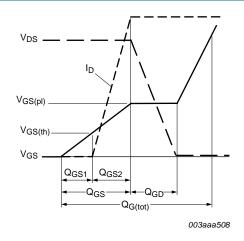
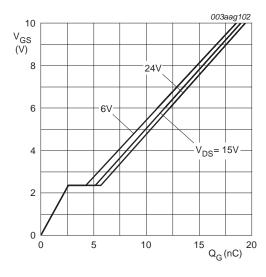
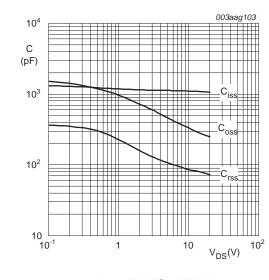


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 20A$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

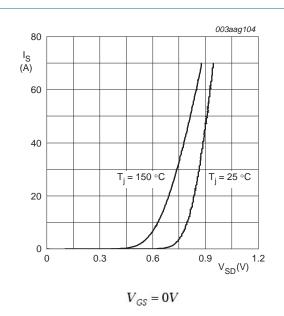


Fig 17. Source current as a function of source-drain voltage; typical values

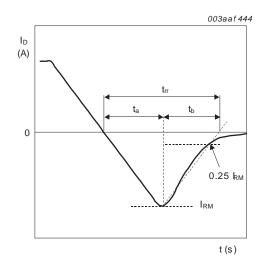
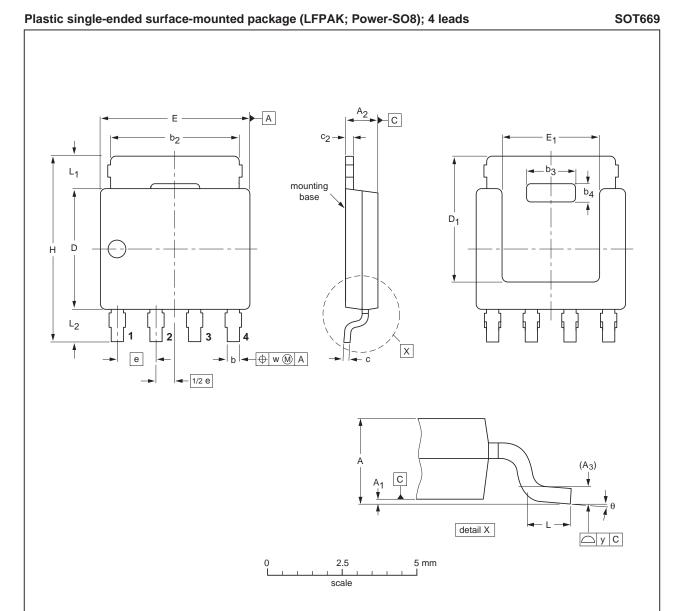


Fig 18. Reverse recovery timing definition

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## 7. Package outline



#### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b	b <sub>2</sub>	b <sub>3</sub>	b <sub>4</sub>	С	c <sub>2</sub>	D <sup>(1)</sup>	D <sub>1</sub> <sup>(1)</sup> max	E <sup>(1)</sup>	E <sub>1</sub> <sup>(1)</sup>	е	Н	L	L <sub>1</sub>	L <sub>2</sub>	w	у	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC JEITA		PROJECTION	ISSUE DATE
SOT669		MO-235			<del>06-03-16</del> 11-03-25

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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**Product data sheet** 

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## 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R0-30YLB v.2	20111024	Product data sheet	-	PSMN6R0-30YLB v.1
Modifications:	<ul> <li>Status changed from</li> </ul>	m preliminary to product.		
	<ul> <li>Various changes to</li> </ul>	content.		
PSMN6R0-30YLB v.1	20110908	Preliminary data sheet	-	-

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### N-channel 30 V 6.5 mΩ logic level MOSFET in LFPAK using NextPower technology

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions'
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## **Nexperia**

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N-channel 30 V 6.5 mΩ logic level MOSFET in LFPAK using NextPower technology

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